

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Leonard Forbes et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	303.356US4
Title:	OPERATING A MEMORY DEVICE		

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INFORMATION DISCLOSURE STATEMENT

MS Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication. Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 08/902133, filed on July 29, 1997, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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27 February 2004

By

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 11

Attorney Docket No: 303.356US4

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Substitute Disclosure Statement Form (PTO-1449)

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown
	Examiner Name	Unknown
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	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown
	Examiner Name	Unknown
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	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 4 of 11	Attorney Docket No: 303.356US4	

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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Sheet 5 of 11	Attorney Docket No: 303.356US4	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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	Group Art Unit	Unknown
	Examiner Name	Unknown
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